Supplementary Information

Solution-processed CuZn_{1-x}Al_xS_2 a new memory material with tuneable electrical bistability

K.B. Jinesh, a* Sudip K. Batabyal, a* R. Devi Chandra and Yizhong Huang

a Energy Research Institute @ NTU (ERI@N), Nanyang Technological University, Research Techno Plaza, Level 5, 50 Nanyang Drive, Singapore 639798.

b School of Material Science and Engineering, Nanyang Technological University, Block N4.1, Nanyang Avenue, Singapore 639798.

SI-1. Electron-beam-induced evolution in the CZAS crystals during HRTEM imaging. (a) lattice oriented along (220) direction; (b) onset of the lattice disturbance due to e-beam; (c) wavy fluctuations in the lattice; (d), (e) onset of evaporation of the material and (f) evaporated regions in a CZAS crystal after imaging.

During the TEM imaging, we could observe fluctuations in the images induced by the electron-beam, followed by evaporation of the material. Figure 5 shows a series of TEM imaging, where Fig. SI-1(a) shows the lattice oriented along (220) direction and (b) shows the onset of the structural changes in the material due to e-beam. Figure SI-1 (c) shows Moiré patterns, which were constantly changing during imaging, because of changes in the films. This is followed by evaporation of the focussed part of the crystal as indicated in Fig. SI-1and (e). Fig. SI-1 (f) shows three regions from where the material was evaporated.